TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA373FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

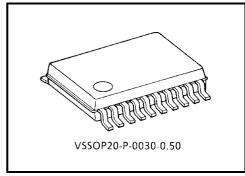
The TC7MA373FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V\!.$

The 8 bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

When the $\overline{\text{OE}}$ input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- Low voltage operation: V_{CC} = 1.8~3.6 V
- High speed operation: $t_{pd} = 4.2 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.7 \text{ ns (max) (VCC} = 2.3 \sim 2.7 \text{ V)}$

 $t_{pd} = 9.4 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $IOH/IOL = \pm 18 \text{ mA (min) (VCC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

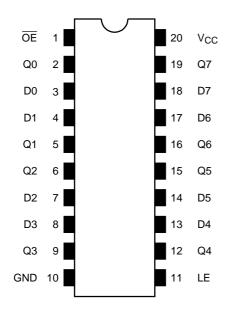
- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model $> \pm 2000 \text{ V}$

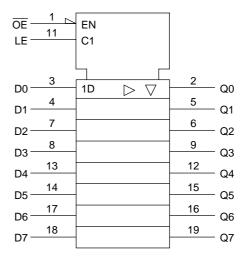
- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)

^{*:} To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Level



Truth Table

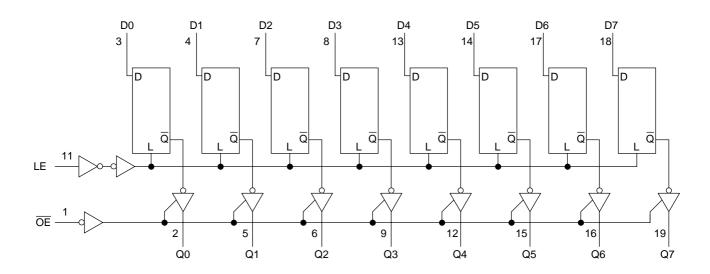
	Inputs					
ŌĒ	LE	D	Outputs			
Н	Х	Х	Z			
L	L	Х	Qn			
L	Н	L	L			
L	Н	Н	Н			

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
DC output voltage	V _{OUT}	-0.5~4.6 (Note1)	V
Do output voltage	٧٥٥١	-0.5~V _{CC} + 0.5 (Note2)	V
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note3)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	1.8~3.6	V	
Supply Voltage	VCC	1.2~3.6 (Note4)	V	
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	\/	0~3.6 (Note5)	V	
Output voltage	Vout	0~V _{CC} (Note6)	V	
		±24 (Note7)		
Output current	I _{OH} /I _{OL}	±18 (Note8)	mA	
		±6 (Note9)		
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note9: $V_{CC} = 1.8 \text{ V}$

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = $-40 \sim 85$ °C, 2.7 V < V_{CC} \leq 3.6 V)

Character	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2		
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				I _{OH} = -18 mA	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
Low level		Vol	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
	Low lovel			$I_{OL} = 12 \text{ mA}$	2.7	_	0.4	
	LOW level	VOL		$I_{OL} = 18 \text{ mA}$	3.0	_	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	_	0.55	
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
2 state output off s	tata current	la-	V _{IN} = V _{IH} or V _{IL}		2.7~3.6	_	±10.0	_
3-state output off-state current		l _{OZ}	V _{OUT} = 0~3.6 V		2.7~3.0		±10.0	μΑ
Power off leakage	current	I _{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6 \text{ V}$		0	_	10.0	μΑ
	Quiescent supply current		V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply o			$V_{CC} \le (V_{IN}, V_{OUT}) \le 3$	V _{CC} ≦ (V _{IN} , V _{OUT}) ≦ 3.6 V		_	±20.0	μΑ
		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$ (per	r input)	2.7~3.6	_	750	

DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit			
la must valta ma	High level	V _{IH}		_	2.3~2.7	1.6	_	V			
Input voltage	Low level	V _{IL}		_	2.3~2.7		0.7	V			
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_				
	High level	Voн	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.3	2.0	_				
				I _{OH} = -12 mA	2.3	1.8	_	V			
Output voltage				I _{OH} = -18 mA	2.3	1.7	_				
		I _{OL} = 100 μA	V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.3~2.7	_	0.2				
	Low level	V_{OL}		$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6				
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μΑ			
2 state output off o			V _{IN} = V _{IH} or V _{IL}		0.2.07		110.0	^			
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.3~2.7		±10.0	μΑ			
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ			
Quioscont supply	current	loo	V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	^			
Quiescent supply current		Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ			

DC Characteristics (Ta = $-40~85^{\circ}$ C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
la mada and la ma	High level	V _{IH}			1.8~2.3	0.7 × V _{CC}	_	
Input voltage	Low level	V _{IL}		_	1.8~2.3	_	0.2 × V _{CC}	V
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage		0		I _{OH} = -6 mA	1.8	1.4	_	V
	Low level		V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	1.8	_	0.2	
	Low level	VOL		$I_{OL} = 6 \text{ mA}$	1.8		0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8		±5.0	μΑ
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μА
Power off leakage c	urrent	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply current			V _{IN} = V _{CC} or GND		1.8	_	20.0	μА
Quiescent supply co	<u></u>	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΑ

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$)

Characteristics Symbol Test Condition			Min	Max	Unit	
Gharacteristics	Characteristics Cymbol 100t Containen		V _{CC} (V)	IVIIII	IVIAX	Offic
	.		1.8	1.5	9.4	
Propagation delay time (D-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	8.0	4.7	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.2	
			1.8	1.5	9.8	
Propagation delay time (LE-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.9	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.2	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	5.5	ns
	t _{pZH}		3.3 ± 0.3	0.6	4.5	
	1	Figure 1, Figure 3	1.8	1.5	6.5	ns
3-state output disable time	t _{pLZ}		2.5 ± 0.2	0.8	3.6	
	t _{pHZ}		3.3 ± 0.3	0.6	3.3	
			1.8	4.0	_	
Minimum pulse width (LE)	t _{w (H)}	w (H) Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	t _s	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	t _{osLH}	(Note11)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

For $C_L = 50\ pF$, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 3.3	0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 1.8	-0.25	
Quiet output minimum dynamic V _{OL}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2) 3.3	2.2	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

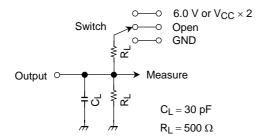
Characteristics	Symbol	Test Condition			Typ	Unit
Characteristics	Syllibol			V _{CC} (V)	Тур.	Offic
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (N	Note13)	1.8, 2.5, 3.3	20	pF

Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	
t _{pHZ} , t _{pZH}	GND

Figure 1

AC Waveform

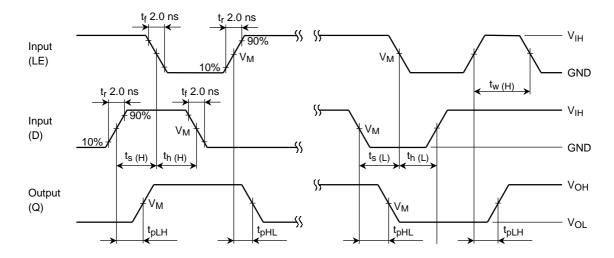


Figure 2 t_{pLH} , t_{pHL} , t_{w} , t_{s} , t_{h}

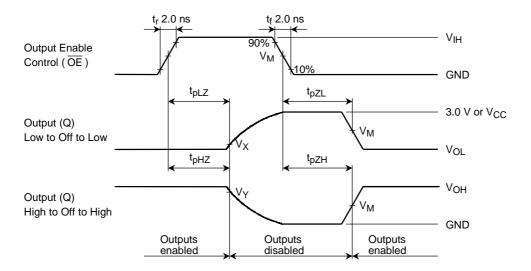


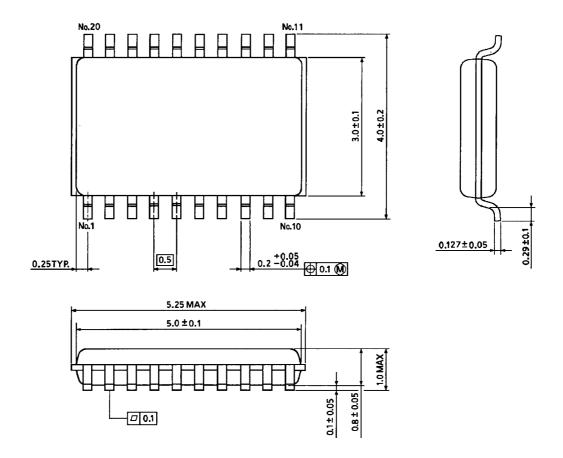
Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol		V_{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	Vcc
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
V _X	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

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Package Dimensions

TOSHIBA



Weight: 0.03 g (typ.)

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